Lattice Semiconductor Corporation - LFE5U-85F-6BG756I Datasheet

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Understanding Embedded - FPGAs (Field Programmable Gate Array)

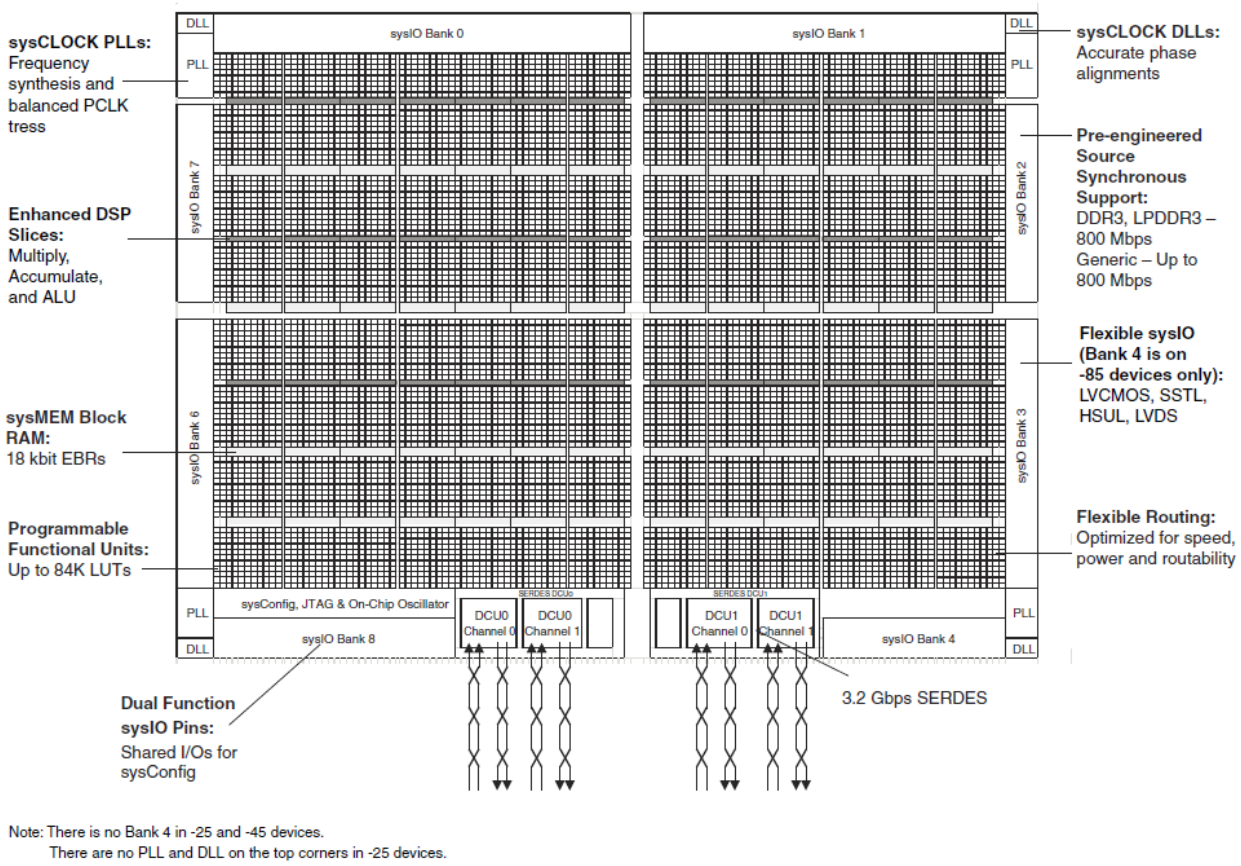
Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Active
Number of LABs/CLBs	21000
Number of Logic Elements/Cells	84000
Total RAM Bits	3833856
Number of I/O	365
Number of Gates	-
Voltage - Supply	1.045V ~ 1.155V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	756-FBGA
Supplier Device Package	756-CABGA (27x27)
Purchase URL	https://www.e-xfl.com/product-detail/lattice-semiconductor/lfe5u-85f-6bg756i

Contents



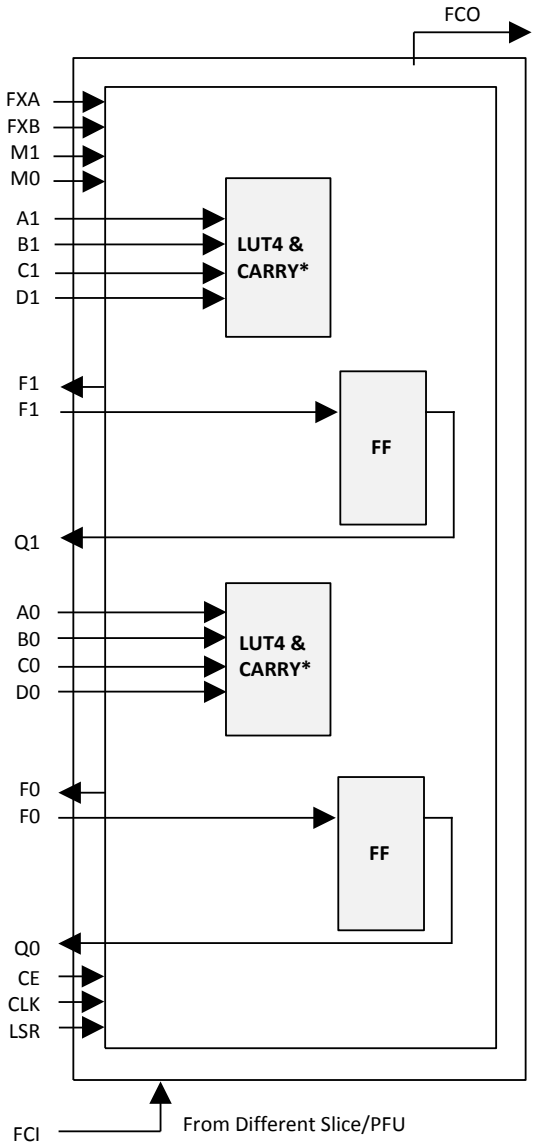
Note: There is no Bank 4 in -25 and -45 devices.
There are no PLL and DLL on the top corners in -25 devices.

Figure 2.1. Simplified Block Diagram, LFE5UM/LFE5UM5G-85 Device (Top Level)

2.2. PFU Blocks

The core of the ECP5/ECP5-5G device consists of PFU blocks. Each PFU block consists of four interconnected slices numbered 0-3, as shown in Figure 2.2. Each slice contains two LUTs. All the interconnections to and from PFU blocks are from routing. There are 50 inputs and 23 outputs associated with each PFU block.

The PFU block can be used in Distributed RAM or ROM function, or used to perform Logic, Arithmetic, or ROM functions. Table 2.1 shows the functions each slice can perform in either mode.



Notes: For Slices 0 and 1, memory control signals are generated from Slice 2 as follows:
WCK is CLK
WRE is from LSR
DI[3:2] for Slice 1 and DI[1:0] for Slice 0 data from Slice 2
WAD [A:D] is a 4-bit address from slice 2 LUT input

Figure 2.3. Slice Diagram

2.2.2. Modes of Operation

Slices 0-2 have up to four potential modes of operation: Logic, Ripple, RAM and ROM. Slice 3 is not needed for RAM mode, it can be used in Logic, Ripple, or ROM modes.

Logic Mode

In this mode, the LUTs in each slice are configured as 4-input combinatorial lookup tables. A LUT4 can have 16 possible input combinations. Any four input logic functions can be generated by programming this lookup table. Since there are two LUT4s per slice, a LUT5 can be constructed within one slice. Larger look-up tables such as LUT6, LUT7 and LUT8 can be constructed by concatenating other slices. Note that LUT8 requires more than four slices.

Ripple Mode

Ripple mode supports the efficient implementation of small arithmetic functions. In ripple mode, the following functions can be implemented by each slice:

- Addition 2-bit
- Subtraction 2-bit
- Add/Subtract 2-bit using dynamic control
- Up counter 2-bit
- Down counter 2-bit
- Up/Down counter with asynchronous clear
- Up/Down counter with preload (sync)
- Ripple mode multiplier building block
- Multiplier support
- Comparator functions of A and B inputs
  - A greater-than-or-equal-to B
  - A not-equal-to B
  - A less-than-or-equal-to B

Ripple Mode includes an optional configuration that performs arithmetic using fast carry chain methods. In this configuration (also referred to as CCU2 mode) two additional signals, Carry Generate and Carry Propagate, are generated on a per slice basis to allow fast arithmetic functions to be constructed by concatenating Slices.

RAM Mode

In this mode, a 16x4-bit distributed single port RAM (SPR) can be constructed in one PFU using each LUT block in Slice 0 and Slice 1 as a 16 x 2-bit memory in each slice. Slice 2 is used to provide memory address and control signals.
A 16 x 2-bit pseudo dual port RAM (PDPR) memory is created in one PFU by using one Slice as the read-write port and the other companion slice as the read-only port. The slice with the read-write port updates the SRAM data contents in both slices at the same write cycle.

ECP5/ECP5-5G devices support distributed memory initialization.

The Lattice design tools support the creation of a variety of different size memories. Where appropriate, the software will construct these using distributed memory primitives that represent the capabilities of the PFU. Table 2.3 lists the number of slices required to implement different distributed RAM primitives. For more information about using RAM in ECP5/ECP5-5G devices, refer to ECP5 and ECP5-5G Memory Usage Guide (TN1264).

Table 2.3. Number of Slices Required to Implement Distributed RAM

	SPR 16 X 4	PDPR 16 X 4
Number of slices	3	6

Note: SPR = Single Port RAM, PDPR = Pseudo Dual Port RAM

ROM Mode

ROM mode uses the LUT logic; hence, Slices 0 through 3 can be used in ROM mode. Preloading is accomplished through the programming interface during PFU configuration.

For more information, refer to ECP5 and ECP5-5G Memory Usage Guide (TN1264).

In Figure 2.15, note that A_ALU, B_ALU and C_ALU are internal signals generated by combining bits from AA, AB, BA BB and C inputs. For further information, refer to ECP5 and ECP5-5G sysDSP Usage Guide (TN1267).

The ECP5/ECP5-5G sysDSP block supports the following basic elements.

- MULT (Multiply)
- MAC (Multiply, Accumulate)
- MULTADDSUB (Multiply, Addition/Subtraction)
- MULTADDSUBSUM (Multiply, Addition/Subtraction, Summation)

Table 2.7 shows the capabilities of each of the ECP5/ECP5-5G slices versus the above functions.

Table 2.7. Maximum Number of Elements in a Slice

Width of Multiply	x9	x18	x36
MULT	4	2	1/2
MAC	1	1	—
MULTADDSUB	2	1	—
MULTADDSUBSUM	1*	1/2	—

***Note**: One slice can implement 1/2 9x9 m9x9addsubsum and two m9x9addsubsum with two slices.

Some options are available in the four elements. The input register in all the elements can be directly loaded or can be loaded as a shift register from previous operand registers. By selecting “dynamic operation” the following operations are possible:

- In the Add/Sub option the Accumulator can be switched between addition and subtraction on every cycle.
- The loading of operands can switch between parallel and serial operations.

For further information, refer to ECP5 and ECP5-5G sysDSP Usage Guide (TN1267).

2.10. Programmable I/O Cells

The programmable logic associated with an I/O is called a PIO. The individual PIO are connected to their respective sysIO buffers and pads. On the ECP5/ECP5-5G devices, the Programmable I/O cells (PIC) are assembled into groups of four PIO cells called a Programmable I/O Cell or PIC. The PICs are placed on all four sides of the device.

On all the ECP5/ECP5-5G devices, two adjacent PIOs can be combined to provide a complementary output driver pair. All PIO pairs can implement differential receivers. Half of the PIO pairs on the left and right edges of these devices can be configured as true LVDS transmit pairs.

2.14. sysI/O Buffer

Each I/O is associated with a flexible buffer referred to as a sysI/O buffer. These buffers are arranged around the periphery of the device in groups referred to as banks. The sysI/O buffers allow users to implement the wide variety of standards that are found in today's systems including LVDS, HSUL, BLVDS, SSTL Class I and II, LVCMOS, LVTTL, LVPECL, and MIPI.

2.14.1. sysI/O Buffer Banks

ECP5/ECP5-5G devices have seven sysI/O buffer banks, two banks per side at Top, Left and Right, plus one at the bottom left side. The bottom left side bank (Bank 8) is a shared I/O bank. The I/Os in that bank contains both dedicated and shared I/O for sysConfig function. When a shared pin is not used for configuration, it is available as a user I/O. For LFE5-85 devices, there is an additional I/O bank (Bank 4) that is not available in other device in the family.

In ECP5/ECP5-5G devices, the Left and Right sides are tailored to support high performance interfaces, such as DDR2, DDR3, LPDDR2, LPDDR3 and other high speed source synchronous standards. The banks on the Left and Right sides of the devices feature LVDS input and output buffers, data-width gearing, and DQSBUF block to support DDR2/3 and LPDDR2/3 interfaces. The I/Os on the top and bottom banks do not have LVDS input and output buffer, and gearing logic, but can use LVCMOS to emulate most of differential output signaling.

Each sysIO bank has its own I/O supply voltage (V_{CCIO}). In addition, the banks on the Left and Right sides of the device, have voltage reference input (shared I/O pin), VREF1 per bank, which allow it to be completely independent of each other. The V_{REF} voltage is used to set the threshold for the referenced input buffers, such as SSTL. Figure 2.25 shows the seven banks and their associated supplies.

In ECP5/ECP5-5G devices, single-ended output buffers and ratioed input buffers (LVTTL, and LVCMOS) are powered using V_{CCIO}. LVTTL, LVCMOS33, LVCMOS25 and LVCMOS12 can also be set as fixed threshold inputs independent of V_{CCIO}.

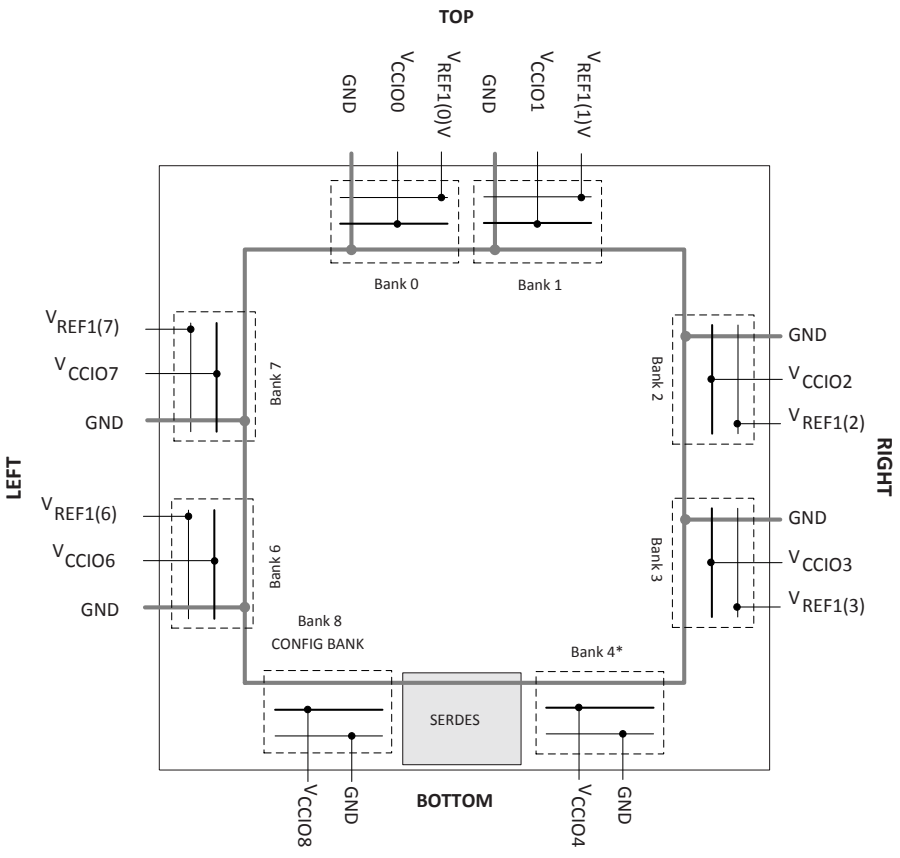


Figure 2.25. ECP5/ECP5-5G Device Family Banks

2.15. SERDES and Physical Coding Sublayer

LFE5UM/LFE5UM5G devices feature up to 4 channels of embedded SERDES/PCS arranged in dual-channel blocks at the bottom of the devices. Each channel supports up to 3.2 Gb/s (ECP5), or up to 5 Gb/s (ECP5-5G) data rate. Figure 2.27 shows the position of the dual blocks for the LFE5-85. Table 2.13 shows the location of available SERDES Duals for all devices. The LFE5UM/LFE5UM5G SERDES/PCS supports a range of popular serial protocols, including:

- PCI Express Gen1 and Gen2 (2.5 Gb/s) on ECP5UM; Gen 1, Gen2 (2.5 Gb/s and 5 Gb/s) on ECP5-5G
- Ethernet (XAUI, GbE – 1000 Base CS/SX/LX and SGMII)
- SMPTE SDI (3G-SDI, HD-SDI, SD-SDI)
- CPRI (E.6.LV: 614.4 Mb/s, E.12.LV: 1228.8 Mb/s, E.24.LV: 2457.6 Mb/s, E.30.LV: 3072 Mb/s), also E.48.LV2:4915 Mb/s in ECP5-5G
- JESD204A/B – ADC and DAC converter interface: 312.5 Mb/s to 3.125 Gb/s (ECP5) / 5 Gb/s (ECP5-5G)

Each dual contains two dedicated SERDES for high speed, full duplex serial data transfer. Each dual also has a PCS block that interfaces to the SERDES channels and contains protocol specific digital logic to support the standards listed above. The PCS block also contains interface logic to the FPGA fabric. All PCS logic for dedicated protocol support can also be bypassed to allow raw 8-bit or 10-bit interfaces to the FPGA fabric.

Even though the SERDES/PCS blocks are arranged in duals, multiple baud rates can be supported within a dual with the use of dedicated, per channel /1, /2 and /11 rate dividers. Additionally, two duals can be arranged together to form x4 channel link.

ECP5UM devices and ECP5-5G devices are pin-to-pin compatible. But, the ECP5UM devices require 1.1 V on VCCA, VCCHRX and VCCHTX supplies. ECP5-5G devices require 1.2 V on these supplies. When designing either family device with migration in mind, these supplies need to be connected such that it is possible to adjust the voltage level on these supplies.

When a SERDES Dual in a 2-Dual device is not used, the power VCCA power supply for that Dual should be connected. It is advised to connect the VCCA of unused channel to core if the user knows he will not use the Dual at all, or it should be connected to a different regulated supply, if that Dual may be used in the future.

For an unused channel in a Dual, it is advised to connect the VCCHTX to VCCA, and user can leave VCCHRX unconnected.

For information on how to use the SERDES/PCS blocks to support specific protocols, as well on how to combine multiple protocols and baud rates within a device, refer to ECP5 and ECP5-5G SERDES/PCS Usage Guide (TN1261).

3. DC and Switching Characteristics

3.1. Absolute Maximum Ratings

Table 3.1. Absolute Maximum Ratings

Symbol	Parameter	Min	Max	Unit
V_{CC}	Supply Voltage	–0.5	1.32	V
V_{CCA}	Supply Voltage	–0.5	1.32	V
V_{CCAUX}, V_{CCAUXA}	Supply Voltage	–0.5	2.75	V
V_{CCIO}	Supply Voltage	–0.5	3.63	V
—	Input or I/O Transient Voltage Applied	–0.5	3.63	V
V_{CCHRX}, V_{CCHTX}	SERDES RX/TX Buffer Supply Voltages	–0.5	1.32	V
—	Voltage Applied on SERDES Pins	–0.5	1.80	V
T_A	Storage Temperature (Ambient)	–65	150	°C
T_J	Junction Temperature	—	+125	°C

Notes:
1. Stress above those listed under the “Absolute Maximum Ratings” may cause permanent damage to the device. Functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.
2. Compliance with the Lattice Thermal Management document is required.
3. All voltages referenced to GND.

3.2. Recommended Operating Conditions

Table 3.2. Recommended Operating Conditions

Symbol	Parameter		Min	Max	Unit
V_{CC}[2]	Core Supply Voltage	ECP5	1.045	1.155	V
		ECP5-5G	1.14	1.26	V
V_{CCAUX}[2, 4]	Auxiliary Supply Voltage	—	2.375	2.625	V
V_{CCIO}[2, 3]	I/O Driver Supply Voltage	—	1.14	3.465	V
V_{REF}[1]	Input Reference Voltage	—	0.5	1.0	V
t_{JCOM}	Junction Temperature, Commercial Operation	—	0	85	°C
t_{JIND}	Junction Temperature, Industrial Operation	—	–40	100	°C
SERDES External Power Supply[5]					
V_{CCA}	SERDES Analog Power Supply	ECP5UM	1.045	1.155	V
		ECP5-5G	1.164	1.236	V
V_{CCAUXA}	SERDES Auxiliary Supply Voltage	—	2.374	2.625	V
V_{CCHRX}[6]	SERDES Input Buffer Power Supply	ECP5UM	0.30	1.155	V
		ECP5-5G	0.30	1.26	V
V_{CCHTX}	SERDES Output Buffer Power Supply	ECP5UM	1.045	1.155	V
		ECP5-5G	1.14	1.26	V

Notes:
1. For correct operation, all supplies except V_{REF} must be held in their valid operation range. This is true independent of feature usage.
2. All supplies with same voltage, except SERDES Power Supplies, should be connected together.
3. See recommended voltages by I/O standard in Table 3.4 on page 48.
4. V_{CCAUX} ramp rate must not exceed 30 mV/µs during power-up when transitioning between 0 V and 3 V.
5. Refer to ECP5 and ECP5-5G SERDES/PCS Usage Guide (TN1261) for information on board considerations for SERDES power supplies.
6. V_{CCHRX} is used for Rx termination. It can be biased to Vcm if external AC coupling is used. This voltage needs to meet all the HDin input voltage level requirements specified in the Rx section of this Data Sheet.

3.11. SERDES Power Supply Requirements[1,2,3]

Over recommended operating conditions.

Table 3.9. ECP5UM

Symbol	Description	Typ	Max	Unit
Standby (Power Down)				
I_{CCA-SB}	V_{CCA} Power Supply Current (Per Channel)	4	9.5	mA
$I_{CCHRX-SB}$[4]	V_{CCHRX}, Input Buffer Current (Per Channel)	—	0.1	mA
$I_{CCHTX-SB}$	V_{CCHTX}, Output Buffer Current (Per Channel)	—	0.9	mA
Operating (Data Rate = 3.125 Gb/s)				
I_{CCA-OP}	V_{CCA} Power Supply Current (Per Channel)	43	54	mA
$I_{CCHRX-OP}$[5]	V_{CCHRX}, Input Buffer Current (Per Channel)	0.4	0.5	mA
$I_{CCHTX-OP}$	V_{CCHTX}, Output Buffer Current (Per Channel)	10	13	mA
Operating (Data Rate = 2.5 Gb/s)				
I_{CCA-OP}	V_{CCA} Power Supply Current (Per Channel)	40	50	mA
$I_{CCHRX-OP}$[5]	V_{CCHRX}, Input Buffer Current (Per Channel)	0.4	0.5	mA
$I_{CCHTX-OP}$	V_{CCHTX}, Output Buffer Current (Per Channel)	10	13	mA
Operating (Data Rate = 1.25 Gb/s)				
I_{CCA-OP}	V_{CCA} Power Supply Current (Per Channel)	34	43	mA
$I_{CCHRX-OP}$[5]	V_{CCHRX}, Input Buffer Current (Per Channel)	0.4	0.5	mA
$I_{CCHTX-OP}$	V_{CCHTX}, Output Buffer Current (Per Channel)	10	13	mA
Operating (Data Rate = 270 Mb/s)				
I_{CCA-OP}	V_{CCA} Power Supply Current (Per Channel)	28	38	mA
$I_{CCHRX-OP}$[5]	V_{CCHRX}, Input Buffer Current (Per Channel)	0.4	0.5	mA
$I_{CCHTX-OP}$	V_{CCHTX}, Output Buffer Current (Per Channel)	8	10	mA

Notes:

1. Rx Equalization enabled, Tx De-emphasis (pre-cursor and post-cursor) disabled
2. Per Channel current is calculated with both channels on in a Dual, and divide current by two. If only one channel is on, current will be higher.
3. To calculate with Tx De-emphasis enabled, use the Diamond Power Calculator tool.
4. For $I_{CCHRX-SB}$, during Standby, input termination on Rx are disabled.
5. For $I_{CCHRX-OP}$, during operational, the max specified when external AC coupling is used. If externally DC coupled, the power is based on current pulled down by external driver when the input is driven to LOW.

3.14.7. **MLVDS25**

The ECP5/ECP5-5G devices support the differential MLVDS standard. This standard is emulated using complementary LVCMOS outputs in conjunction with a parallel resistor across the driver outputs. The MLVDS input standard is supported by the LVDS differential input buffer. The scheme shown in Figure 3.4 is one possible solution for MLVDS standard implementation. Resistor values in the figure are industry standard values for 1% resistors.

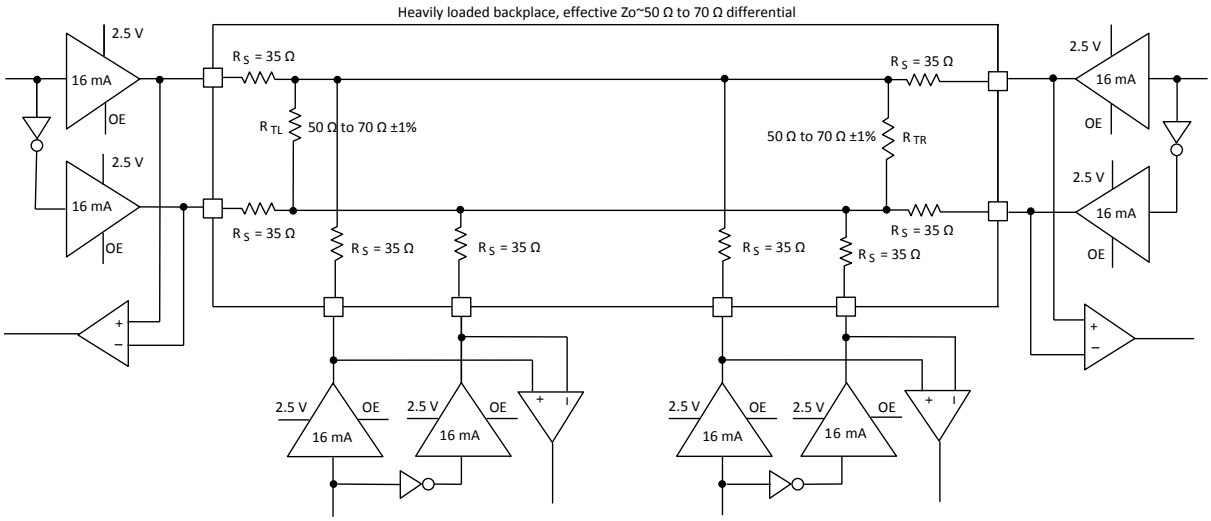


Figure 3.4. MLVDS25 (Multipoint Low Voltage Differential Signaling)

Table 3.17. MLVDS25 DC Conditions

Parameter	Description	Typical		Unit
		Zo=50 Ω	Zo=70 Ω	
V_{CCIO}	Output Driver Supply (±5%)	2.50	2.50	V
Z_{OUT}	Driver Impedance	10.00	10.00	Ω
R_S	Driver Series Resistor (±1%)	35.00	35.00	Ω
R_{TL}	Driver Parallel Resistor (±1%)	50.00	70.00	Ω
R_{TR}	Receiver Termination (±1%)	50.00	70.00	Ω
V_{OH}	Output High Voltage	1.52	1.60	V
V_{OL}	Output Low Voltage	0.98	0.90	V
V_{OD}	Output Differential Voltage	0.54	0.70	V
V_{CM}	Output Common Mode Voltage	1.25	1.25	V
I_{DC}	DC Output Current	21.74	20.00	mA

Note: For input buffer, see LVDS Table 3.13 on page 55.

Table 3.20. Register-to-Register Performance

Function	–8 Timing	Unit
Basic Functions		
16-Bit Decoder	441	MHz
32-Bit Decoder	441	MHz
64-Bit Decoder	332	MHz
4:1 Mux	441	MHz
8:1 Mux	441	MHz
16:1 Mux	441	MHz
32:1 Mux	441	MHz
8-Bit Adder	441	MHz
16-Bit Adder	441	MHz
64-Bit Adder	441	MHz
16-Bit Counter	384	MHz
32-Bit Counter	317	MHz
64-Bit Counter	263	MHz
64-Bit Accumulator	288	MHz
Embedded Memory Functions		
1024x18 True-Dual Port RAM (Write Through or Normal), with EBR Output Registers	272	MHz
1024x18 True-Dual Port RAM (Read-Before-Write), with EBR Output Registers	214	MHz
Distributed Memory Functions		
16 x 2 Pseudo-Dual Port or 16 x 4 Single Port RAM (One PFU)	441	MHz
16 x 4 Pseudo-Dual Port (Two PFUs)	441	MHz
DSP Functions		
9 x 9 Multiplier (All Registers)	225	MHz
18 x 18 Multiplier (All Registers)	225	MHz
36 x 36 Multiplier (All Registers)	225	MHz
18 x 18 Multiply-Add/Sub (All Registers)	225	MHz
18 x 18 Multiply/Accumulate (Input and Output Registers)	225	MHz

Notes:

1. These functions were generated using Lattice Diamond design software tool. Exact performance may vary with the device and the design software tool version. The design software tool uses internal parameters that have been characterized but are not tested on every device.
2. Commercial timing numbers are shown. Industrial numbers are typically slower and can be extracted from Lattice Diamond design software tool.

3.16. Derating Timing Tables

Logic timing provided in the following sections of this data sheet and the Diamond design tools are worst case numbers in the operating range. Actual delays at nominal temperature and voltage for best case process, can be much better than the values given in the tables. The Diamond design tool can provide logic timing numbers at a particular temperature and voltage.

3.17. Maximum I/O Buffer Speed

Over recommended operating conditions.

Table 3.21. ECP5/ECP5-5G Maximum I/O Buffer Speed

Buffer	Description	Max	Unit
Maximum Input Frequency			
LVDS25	LVDS, V_{CCIO} = 2.5 V	400	MHz
MLVDS25	MLVDS, Emulated, V_{CCIO} = 2.5 V	400	MHz
BLVDS25	BLVDS, Emulated, V_{CCIO} = 2.5 V	400	MHz
MIPI D-PHY (HS Mode)	MIPI Video	400	MHz
SLVS	SLVS similar to MIPI	400	MHz
Mini LVDS	Mini LVDS	400	MHz
LVPECL33	LVPECL, Emulated, V_{CCIO} = 3.3 V	400	MHz
SSTL18 (all supported classes)	SSTL_18 class I, II, V_{CCIO} = 1.8 V	400	MHz
SSTL15 (all supported classes)	SSTL_15 class I, II, V_{CCIO} = 1.5 V	400	MHz
SSTL135 (all supported classes)	SSTL_135 class I, II, V_{CCIO} = 1.35 V	400	MHz
HSUL12 (all supported classes)	HSUL_12 class I, II, V_{CCIO} = 1.2 V	400	MHz
LVTTL33	LVTTL, V_{CCIO} = 3.3 V	200	MHz
LVCMOS33	LVCMOS, V_{CCIO} = 3.3 V	200	MHz
LVCMOS25	LVCMOS, V_{CCIO} = 2.5 V	200	MHz
LVCMOS18	LVCMOS, V_{CCIO} = 1.8 V	200	MHz
LVCMOS15	LVCMOS 1.5, V_{CCIO} = 1.5 V	200	MHz
LVCMOS12	LVCMOS 1.2, V_{CCIO} = 1.2 V	200	MHz
Maximum Output Frequency			
LVDS25E	LVDS, Emulated, V_{CCIO} = 2.5 V	150	MHz
LVDS25	LVDS, V_{CCIO} = 2.5 V	400	MHz
MLVDS25	MLVDS, Emulated, V_{CCIO} = 2.5 V	150	MHz
BLVDS25	BLVDS, Emulated, V_{CCIO} = 2.5 V	150	MHz
LVPECL33	LVPECL, Emulated, V_{CCIO} = 3.3 V	150	MHz
SSTL18 (all supported classes)	SSTL_18 class I, II, V_{CCIO} = 1.8 V	400	MHz
SSTL15 (all supported classes)	SSTL_15 class I, II, V_{CCIO} = 1.5 V	400	MHz
SSTL135 (all supported classes)	SSTL_135 class I, II, V_{CCIO} = 1.35 V	400	MHz
HSUL12 (all supported classes)	HSUL12 class I, II, V_{CCIO} = 1.2 V	400	MHz
LVTTL33	LVTTL, VCCIO = 3.3 V	150	MHz
LVCMOS33 (For all drives)	LVCMOS, 3.3 V	150	MHz
LVCMOS25 (For all drives)	LVCMOS, 2.5 V	150	MHz
LVCMOS18 (For all drives)	LVCMOS, 1.8 V	150	MHz
LVCMOS15 (For all drives)	LVCMOS, 1.5 V	150	MHz
LVCMOS12 (For all drives)	LVCMOS, 1.2 V	150	MHz

Notes:

1. These maximum speeds are characterized but not tested on every device.
2. Maximum I/O speed for differential output standards emulated with resistors depends on the layout.
3. LVCMOS timing is measured with the load specified in Switching Test Conditions, Table 3.44 on page 90.
4. All speeds are measured at fast slew.
5. Actual system operation may vary depending on user logic implementation.
6. Maximum data rate equals 2 times the clock rate when utilizing DDR.

Parameter	Description	Device	–8		–7		–6		Unit
			Min	Max	Min	Max	Min	Max	
f_{DATA_DDR2} f_{DATA_DDR3} f_{DATA_DDR3L} f_{DATA_LPDDR2} f_{DATA_LPDDR3}	DDR Memory Data Rate	All Devices	—	800	—	700	—	624	Mb/s
f_{MAX_DDR2} f_{MAX_DDR3} f_{MAX_DDR3L} f_{MAX_LPDDR2} f_{MAX_LPDDR3}	DDR Memory CLK Frequency (ECLK)	All Devices	—	400	—	350	—	312	MHz
DDR2/DDR3/DDR3L/LPDDR2/LPDDR3 WRITE (DQ Output Data are Centered to DQS)									
t_{DQVBS_DDR2} t_{DQVBS_DDR3} t_{DQVBS_DDR3L} t_{DQVBS_LPDDR2} t_{DQVBS_LPDDR3}	Data Output Valid before DQS Output	All Devices	—	–0.25	—	–0.25	—	-0.25	UI
t_{DQVAS_DDR2} t_{DQVAS_DDR3} t_{DQVAS_DDR3L} t_{DQVAS_LPDDR2} t_{DQVAS_LPDDR3}	Data Output Valid after DQS Output	All Devices	0.25	—	0.25	—	0.25	—	UI
f_{DATA_DDR2} f_{DATA_DDR3} f_{DATA_DDR3L} f_{DATA_LPDDR2} f_{DATA_LPDDR3}	DDR Memory Data Rate	All Devices	—	800	—	700	—	624	Mb/s
f_{MAX_DDR2} f_{MAX_DDR3} f_{MAX_DDR3L} f_{MAX_LPDDR2} f_{MAX_LPDDR3}	DDR Memory CLK Frequency (ECLK)	All Devices	—	400	—	350	—	312	MHz

Notes:

1. Commercial timing numbers are shown. Industrial numbers are typically slower and can be extracted from the Diamond software.
2. General I/O timing numbers are based on LVCMOS 2.5, 12 mA, Fast Slew Rate, 0pf load.
   Generic DDR timing are numbers based on LVDS I/O.
   DDR2 timing numbers are based on SSTL18.
   DDR3 timing numbers are based on SSTL15.
   LPDDR2 and LPDDR3 timing numbers are based on HSUL12.
3. Uses LVDS I/O standard for measurements.
4. Maximum clock frequencies are tested under best case conditions. System performance may vary upon the user environment.
5. All numbers are generated with the Diamond software.

3.19. sysCLOCK PLL Timing

Over recommended operating conditions.

Table 3.23. sysCLOCK PLL Timing

Parameter	Descriptions	Conditions	Min	Max	Units
f_{IN}	Input Clock Frequency (CLKI, CLKFB)	—	8	400	MHz
f_{OUT}	Output Clock Frequency (CLKOP, CLKOS)	—	3.125	400	MHz
f_{VCO}	PLL VCO Frequency	—	400	800	MHz
f_{PFD}[3]	Phase Detector Input Frequency	—	10	400	MHz
AC Characteristics					
t_{DT}	Output Clock Duty Cycle	—	45	55	%
t_{PH4}	Output Phase Accuracy	—	–5	5	%
t_{OPJIT}[1]	Output Clock Period Jitter	$f_{OUT} \geq 100$ MHz	—	100	ps p-p
		$f_{OUT} < 100$ MHz	—	0.025	UIPP
	Output Clock Cycle-to-Cycle Jitter	$f_{OUT} \geq 100$ MHz	—	200	ps p-p
		$f_{OUT} < 100$ MHz	—	0.050	UIPP
	Output Clock Phase Jitter	$f_{PFD} \geq 100$ MHz	—	200	ps p-p
		$f_{PFD} < 100$ MHz	—	0.011	UIPP
t_{SPO}	Static Phase Offset	Divider ratio = integer	—	400	ps p-p
t_W	Output Clock Pulse Width	At 90% or 10%	0.9	—	ns
t_{LOCK}[2]	PLL Lock-in Time	—	—	15	ms
t_{UNLOCK}	PLL Unlock Time	—	—	50	ns
t_{IPJIT}	Input Clock Period Jitter	$f_{PFD} \geq 20$ MHz	—	1,000	ps p-p
		$f_{PFD} < 20$ MHz	—	0.02	UIPP
t_{HI}	Input Clock High Time	90% to 90%	0.5	—	ns
t_{LO}	Input Clock Low Time	10% to 10%	0.5	—	ns
t_{RST}	RST/ Pulse Width	—	1	—	ms
t_{RSTREC}	RST Recovery Time	—	1	—	ns
t_{LOAD_REG}	Min Pulse for CIB_LOAD_REG	—	10	—	ns
$t_{ROTATE-SETUP}$	Min time for CIB dynamic phase controls to be stable fore CIB_ROTATE	—	5	—	ns
$t_{ROTATE-WD}$	Min pulse width for CIB_ROTATE to maintain “0” or	—	4	—	VCO cycles

Notes:

1. Jitter sample is taken over 10,000 samples for Periodic jitter, and 2,000 samples for Cycle-to-Cycle jitter of the primary PLL output with clean reference clock with no additional I/O toggling.
2. Output clock is valid after t_{LOCK} for PLL reset and dynamic delay adjustment.
3. Period jitter and cycle-to-cycle jitter numbers are guaranteed for $f_{PFD} > 10$ MHz. For $f_{PFD} < 10$ MHz, the jitter numbers may not be met in certain conditions.

3.22. SERDES High-Speed Data Receiver

Table 3.27. Serial Input Data Specifications

Symbol	Description	Min	Typ	Max	Unit
$V_{RX-DIFF-S}$	Differential input sensitivity	150	—	1760	mV, p-p
V_{RX-IN}	Input levels	0	—	V_{CCA} +0.5[2]	V
$V_{RX-CM-DCCM}$	Input common mode range (internal DC coupled mode)	0.6	—	V_{CCA}	V
$V_{RX-CM-ACCM}$	Input common mode range (internal AC coupled mode)[2]	0.1	—	V_{CCA} +0.2	V
$T_{RX-RELOCK}$	SCDR re-lock time[1]	—	1000	—	Bits
$Z_{RX-TERM}$	Input termination 50/75 Ω /High Z	–20%	50/75/5 K	+20%	Ω
RL_{RX-RL}	Return loss (without package)	—	—	–10	dB

Notes:
1. This is the typical number of bit times to re-lock to a new phase or frequency within ±300 ppm, assuming 8b10b encoded data.
2. Up to 1.655 for ECP5, and 1.76 for ECP5-5G.

3.23. Input Data Jitter Tolerance

A receiver's ability to tolerate incoming signal jitter is very dependent on jitter type. High speed serial interface standards have recognized the dependency on jitter type and have specifications to indicate tolerance levels for different jitter types as they relate to specific protocols. Sinusoidal jitter is considered to be a worst case jitter type.

Table 3.28. Receiver Total Jitter Tolerance Specification

Description	Frequency	Condition	Min	Typ	Max	Unit
Deterministic	5 Gb/s	400 mV differential eye	—	—	TBD	UI, p-p
Random		400 mV differential eye	—	—	TBD	UI, p-p
Total		400 mV differential eye	—	—	TBD	UI, p-p
Deterministic	3.125 Gb/s	400 mV differential eye	—	—	0.37	UI, p-p
Random		400 mV differential eye	—	—	0.18	UI, p-p
Total		400 mV differential eye	—	—	0.65	UI, p-p
Deterministic	2.5 Gb/s	400 mV differential eye	—	—	0.37	UI, p-p
Random		400 mV differential eye	—	—	0.18	UI, p-p
Total		400 mV differential eye	—	—	0.65	UI, p-p
Deterministic	1.25 Gb/s	400 mV differential eye	—	—	0.37	UI, p-p
Random		400 mV differential eye	—	—	0.18	UI, p-p
Total		400 mV differential eye	—	—	0.65	UI, p-p

Notes:
1. Jitter tolerance measurements are done with protocol compliance tests: 3.125 Gb/s - XAUI Standard, 2.5 Gb/s - PCIe Standard, 1.25 Gb/s - SGMII Standard.
2. For ECP5-5G family devices only.

3.27. XAUI/CPRI LV E.30 Electrical and Timing Characteristics

3.27.1. AC and DC Characteristics

Over recommended operating conditions.

Table 3.33. Transmit

Symbol	Description	Test Conditions	Min	Typ	Max	Unit
T_{RF}	Differential rise/fall time	20% to 80%	—	80	—	ps
$Z_{TX\_DIFF\_DC}$	Differential impedance	—	80	100	120	Ω
J_{TX_DDJ}[2, 3]	Output data deterministic jitter	—	—	—	0.17	UI
J_{TX_TJ}[1, 2, 3]	Total output data jitter	—	—	—	0.35	UI

Notes:
1. Total jitter includes both deterministic jitter and random jitter.
2. Jitter values are measured with each CML output AC coupled into a 50 Ω impedance (100 Ω differential impedance).
3. Jitter and skew are specified between differential crossings of the 50% threshold of the reference signal.

Over recommended operating conditions.

Table 3.34. Receive and Jitter Tolerance

Symbol	Description	Test Conditions	Min	Typ	Max	Unit
RL_{RX_DIFF}	Differential return loss	From 100 MHz to 3.125 GHz	10	—	—	dB
RL_{RX_CM}	Common mode return loss	From 100 MHz to 3.125 GHz	6	—	—	dB
Z_{RX_DIFF}	Differential termination resistance	—	80	100	120	Ω
J_{RX_DJ}[1, 2, 3]	Deterministic jitter tolerance (peak-to-peak)	—	—	—	0.37	UI
J_{RX_RJ}[1, 2, 3]	Random jitter tolerance (peak-to-peak)	—	—	—	0.18	UI
J_{RX_SJ}[1, 2, 3]	Sinusoidal jitter tolerance (peak-to-peak)	—	—	—	0.10	UI
J_{RX_TJ}[1, 2, 3]	Total jitter tolerance (peak-to-peak)	—	—	—	0.65	UI
T_{RX_EYE}	Receiver eye opening	—	0.35	—	—	UI

Notes:
1. Total jitter includes deterministic jitter, random jitter and sinusoidal jitter.
2. Jitter values are measured with each high-speed input AC coupled into a 50 Ω impedance.
3. Jitter and skew are specified between differential crossings of the 50% threshold of the reference signal.

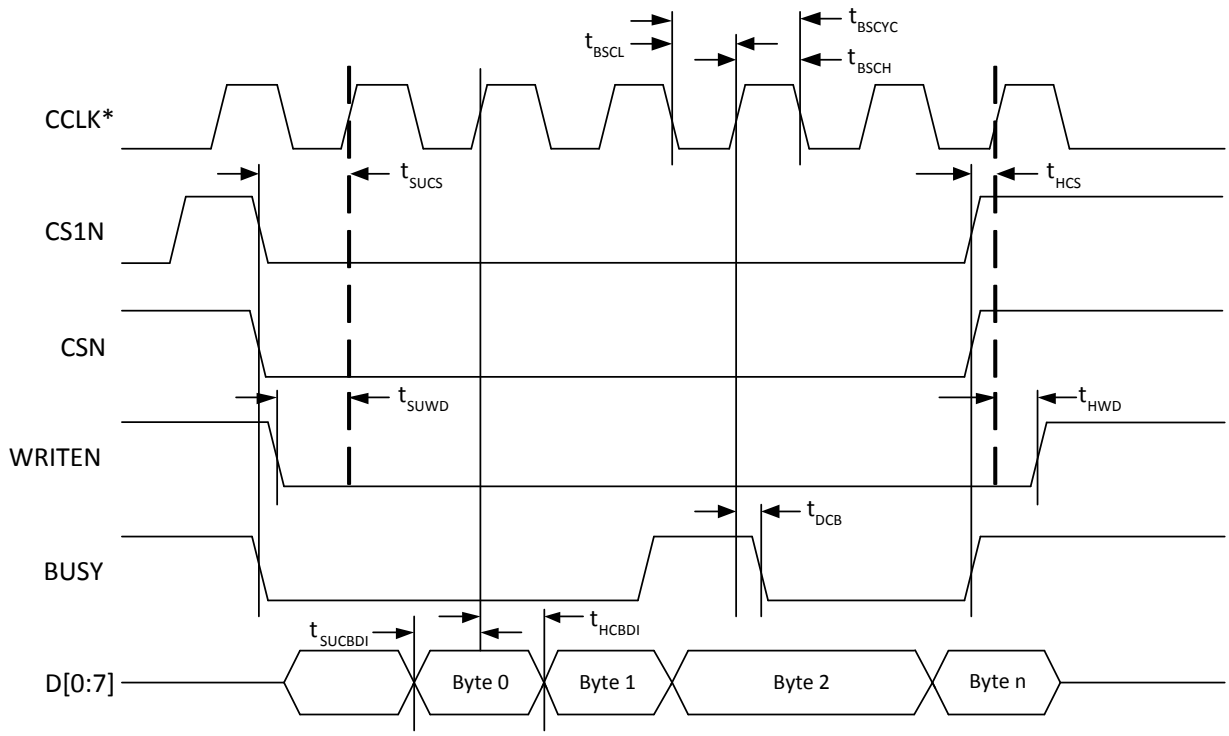
3.28. CPRI LV E.24/SGMII(2.5Gbps) Electrical and Timing Characteristics

3.28.1. AC and DC Characteristics

Table 3.35. Transmit

Symbol	Description	Test Conditions	Min	Typ	Max	Unit
T_{RF}[1]	Differential rise/fall time	20% to 80%	—	80	—	ps
$Z_{TX\_DIFF\_DC}$	Differential impedance	—	80	100	120	Ω
J_{TX_DDJ}[3, 4]	Output data deterministic jitter	—	—	—	0.17	UI
J_{TX_TJ}[2, 3, 4]	Total output data jitter	—	—	—	0.35	UI

Notes:
1. Rise and Fall times measured with board trace, connector and approximately 2.5 pf load.
2. Total jitter includes both deterministic jitter and random jitter. The random jitter is the total jitter minus the actual deterministic jitter.
3. Jitter values are measured with each CML output AC coupled into a 50 Ω impedance (100 Ω differential impedance).
4. Jitter and skew are specified between differential crossings of the 50% threshold of the reference signal.



*In Master Parallel Mode the FPGA provides CCLK (MCLK). In Slave Parallel Mode the external device provides CCLK.

Figure 3.16. sysCONFIG Parallel Port Write Cycle

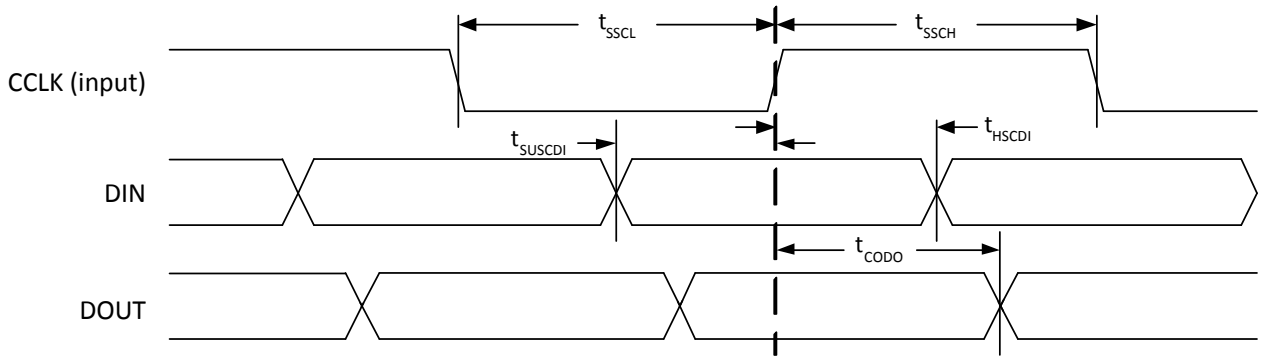


Figure 3.17. sysCONFIG Slave Serial Port Timing

4.2. PICs and DDR Data (DQ) Pins Associated with the DDR Strobe (DQS) Pin

PICs Associated with DQS Strobe	PIO within PIC	DDR Strobe (DQS) and Data (DQ) Pins
For Left and Right Edges of the Device Only		
P[L/R] [n–6]	A	DQ
	B	DQ
	C	DQ
	D	DQ
P[L/R] [n–3]	A	DQ
	B	DQ
	C	DQ
	D	DQ
P[L/R] [n]	A	DQS (P)
	B	DQS (N)
	C	DQ
	D	DQ
P[L/R] [n+3]	A	DQ
	B	DQ
	C	DQ
	D	DQ

Note: "n" is a row PIC number.

4.3. Pin Information Summary

4.3.1. LFE5UM/LFE5UM5G

Pin Information Summary		LFE5UM/ LFE5UM5G-25		LFE5UM/LFE5UM5G-45			LFE5UM/LFE5UM5G-85			
Pin Type		285 csfBG	381 caBGA	285 csfBGA	381 caBG	554 caBGA	285 csfBGA	381 caBG	554 caBGA	756 caBGA
General Purpose Inputs/Outputs per Bank	Bank 0	6	24	6	27	32	6	27	32	56
	Bank 1	6	32	6	33	40	6	33	40	48
	Bank 2	21	32	21	32	32	21	34	32	48
	Bank 3	28	32	28	33	48	28	33	48	64
	Bank 4	0	0	0	0	0	0	0	14	24
	Bank 6	26	32	26	33	48	26	33	48	64
	Bank 7	18	32	18	32	32	18	32	32	48
	Bank 8	13	13	13	13	13	13	13	13	13
Total Single-Ended User I/O		118	197	118	203	245	118	205	259	365
VCC		13	20	13	20	24	13	20	24	36
VCCAUX (Core)		3	4	3	4	9	3	4	9	8
VCCIO	Bank 0	1	2	1	2	3	1	2	3	4
	Bank 1	1	2	1	2	3	1	2	3	4
	Bank 2	2	3	2	3	4	2	3	4	4
	Bank 3	2	3	2	3	3	2	3	3	4
	Bank 4	0	0	0	0	0	0	0	2	2
	Bank 6	2	3	2	3	4	2	3	4	4
	Bank 7	2	3	2	3	3	2	3	3	4
	Bank 8	2	2	2	2	2	2	2	2	2

Part number	Grade	Package	Pins	Temp.	LUTs (K)	SERDES
LFE5U-85F-6BG756I	–6	Lead free caBGA	756	Industrial	84	No
LFE5U-85F-7BG756I	–7	Lead free caBGA	756	Industrial	84	No
LFE5U-85F-8BG756I	–8	Lead free caBGA	756	Industrial	84	No
LFE5UM-25F-6MG285I	–6	Lead free csfBGA	285	Industrial	24	Yes
LFE5UM-25F-7MG285I	–7	Lead free csfBGA	285	Industrial	24	Yes
LFE5UM-25F-8MG285I	–8	Lead free csfBGA	285	Industrial	24	Yes
LFE5UM-25F-6BG381I	–6	Lead free caBGA	381	Industrial	24	Yes
LFE5UM-25F-7BG381I	–7	Lead free caBGA	381	Industrial	24	Yes
LFE5UM-25F-8BG381I	–8	Lead free caBGA	381	Industrial	24	Yes
LFE5UM-45F-6MG285I	–6	Lead free csfBGA	285	Industrial	44	Yes
LFE5UM-45F-7MG285I	–7	Lead free csfBGA	285	Industrial	44	Yes
LFE5UM-45F-8MG285I	–8	Lead free csfBGA	285	Industrial	44	Yes
LFE5UM-45F-6BG381I	–6	Lead free caBGA	381	Industrial	44	Yes
LFE5UM-45F-7BG381I	–7	Lead free caBGA	381	Industrial	44	Yes
LFE5UM-45F-8BG381I	–8	Lead free caBGA	381	Industrial	44	Yes
LFE5UM-45F-6BG554I	–6	Lead free caBGA	554	Industrial	44	Yes
LFE5UM-45F-7BG554I	–7	Lead free caBGA	554	Industrial	44	Yes
LFE5UM-45F-8BG554I	–8	Lead free caBGA	554	Industrial	44	Yes
LFE5UM-85F-6MG285I	–6	Lead free csfBGA	285	Industrial	84	Yes
LFE5UM-85F-7MG285I	–7	Lead free csfBGA	285	Industrial	84	Yes
LFE5UM-85F-8MG285I	–8	Lead free csfBGA	285	Industrial	84	Yes
LFE5UM-85F-6BG381I	–6	Lead free caBGA	381	Industrial	84	Yes
LFE5UM-85F-7BG381I	–7	Lead free caBGA	381	Industrial	84	Yes
LFE5UM-85F-8BG381I	–8	Lead free caBGA	381	Industrial	84	Yes
LFE5UM-85F-6BG554I	–6	Lead free caBGA	554	Industrial	84	Yes
LFE5UM-85F-7BG554I	–7	Lead free caBGA	554	Industrial	84	Yes
LFE5UM-85F-8BG554I	–8	Lead free caBGA	554	Industrial	84	Yes
LFE5UM-85F-6BG756I	–6	Lead free caBGA	756	Industrial	84	Yes
LFE5UM-85F-7BG756I	–7	Lead free caBGA	756	Industrial	84	Yes
LFE5UM-85F-8BG756I	–8	Lead free caBGA	756	Industrial	84	Yes
LFE5UM5G-25F-8MG285I	–8	Lead free csfBGA	285	Industrial	24	Yes
LFE5UM5G-25F-8BG381I	–8	Lead free caBGA	381	Industrial	24	Yes
LFE5UM5G-45F-8MG285I	–8	Lead free csfBGA	285	Industrial	44	Yes
LFE5UM5G-45F-8BG381I	–8	Lead free caBGA	381	Industrial	44	Yes
LFE5UM5G-45F-8BG554I	–8	Lead free caBGA	554	Industrial	44	Yes
LFE5UM5G-85F-8MG285I	–8	Lead free csfBGA	285	Industrial	84	Yes
LFE5UM5G-85F-8BG381I	–8	Lead free caBGA	381	Industrial	84	Yes
LFE5UM5G-85F-8BG554I	–8	Lead free caBGA	554	Industrial	84	Yes
LFE5UM5G-85F-8BG756I	–8	Lead free caBGA	756	Industrial	84	Yes